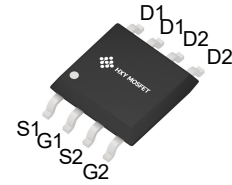




Description

The HXY4882S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

$V_{DS} = 40V$ $I_D = 8A$

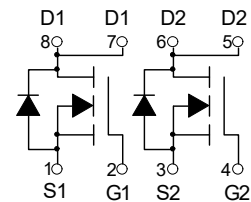
$R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

Ordering Information

| Product ID | Pack | Brand | Qty(PCS) |
|------------|-------|------------|----------|
| HXY4882S | SOP-8 | HXY MOSFET | 3000 |

Absolute Maximum Ratings@ $T_J=25^\circ C$ (unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|----------------------|---|------------|--------------|
| V_{DS} | Drain-Source Voltage | 40 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_A=25^\circ C$ | Drain Current, $V_{GS} @ 4.5V^3$ | 8 | A |
| $I_D@T_A=70^\circ C$ | Drain Current, $V_{GS} @ 4.5V^3$ | 6 | A |
| I_{DM} | Pulsed Drain Current ¹ | 36 | A |
| $P_D@T_A=25^\circ C$ | Total Power Dissipation | 1.9 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |
| R_{thj-a} | Maximum Thermal Resistance, Junction-ambient ³ | 40 | $^\circ C/W$ |



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|------------------------|--|--|------|-------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 40 | --- | --- | V |
| ΔBV _{DSS} /ΔT | BVDSS Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.032 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =7A | --- | 16 | 20 | mΩ |
| | | V _{GS} =4.5V, I _D =6A | --- | 20 | 26 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1.2 | 1.6 | 2.5 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -4.8 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =32V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =32V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =7A | --- | 32 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 2.1 | --- | Ω |
| Q _g | Total Gate Charge (4.5V) | V _{DS} =32V, V _{GS} =4.5V, I _D =7A | --- | 9.8 | --- | nC |
| Q _{gs} | Gate-Source Charge | | --- | 2.8 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 3.9 | --- | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =20V, V _{GS} =10V, R _G =3.3Ω I _D =7A | --- | 2.8 | --- | ns |
| T _r | Rise Time | | --- | 40.4 | --- | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 22.8 | --- | |
| T _f | Fall Time | | --- | 6.4 | --- | |
| C _{iSS} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1MHz | --- | 1013 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 107 | --- | |
| C _{rSS} | Reverse Transfer Capacitance | | --- | 76 | --- | |

Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|---|------|------|------|------|
| I _S | Continuous Source Current ^{1,5} | V _G =V _D =0V, Force Current | --- | --- | 8 | A |
| I _{SM} | Pulsed Source Current ^{2,5} | | --- | --- | 36 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1 | V |
| t _{rr} | Reverse Recovery Time | I _F =7A, dI/dt=100A/μs, T _J =25°C | --- | 10 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 3.3 | --- | nC |

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=25A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

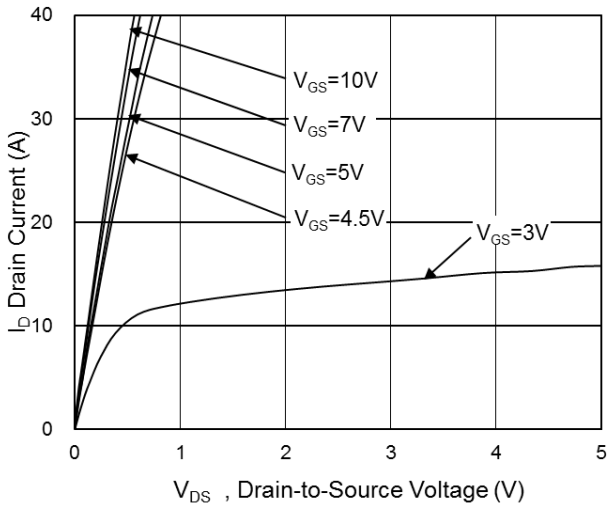


Fig.1 Typical Output Characteristics

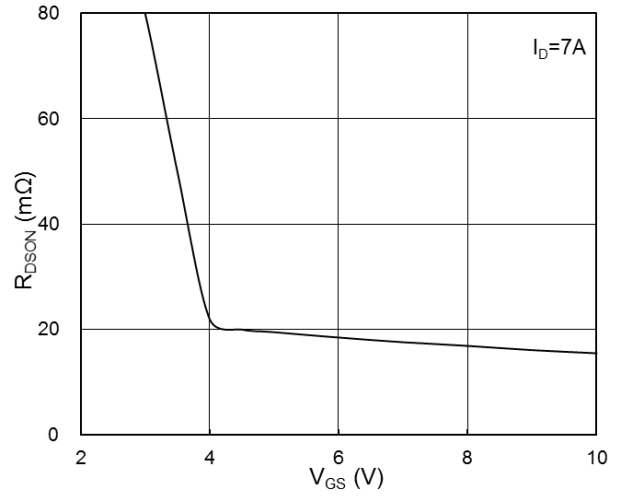


Fig.2 On-Resistance vs. G-S Voltage

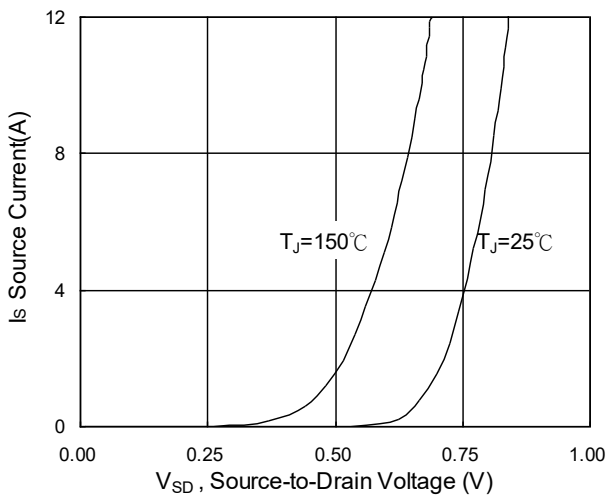


Fig.3 Forward Characteristics of Reverse

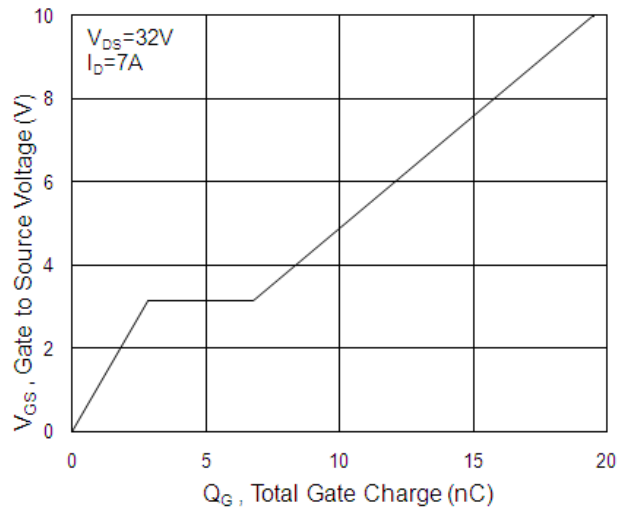


Fig.4 Gate-Charge Characteristics

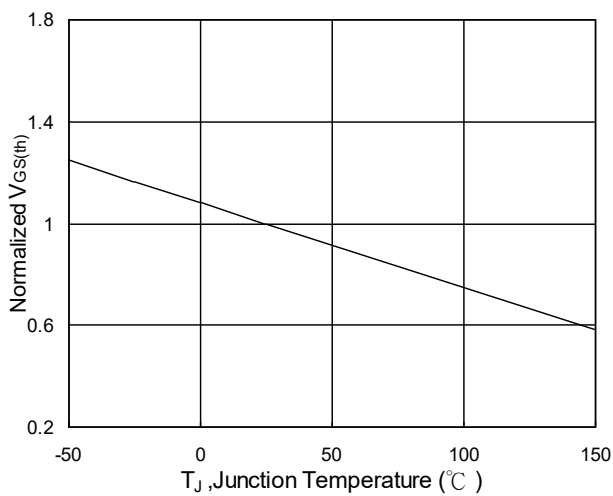


Fig.5 Normalized V_{GS(th)} vs. T_J

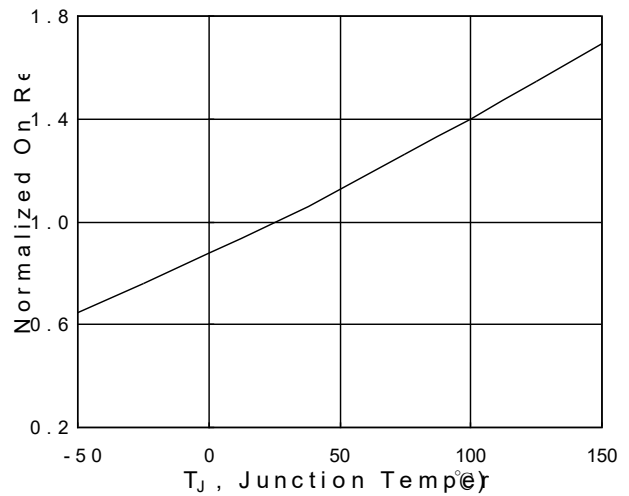


Fig.6 Normalized R_{DS(on)} vs. T_J

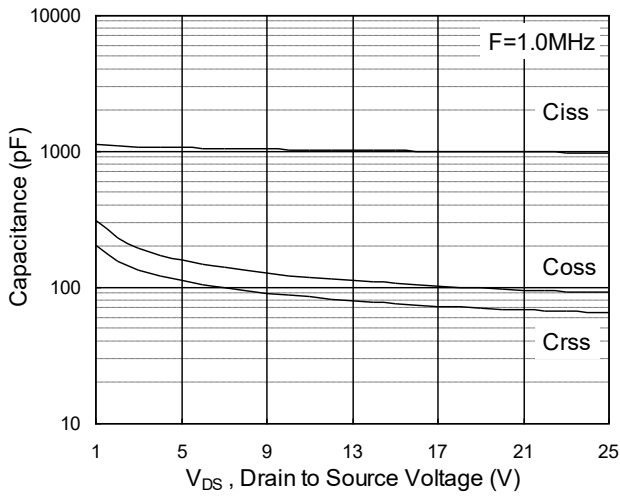


Fig.7 Capacitance

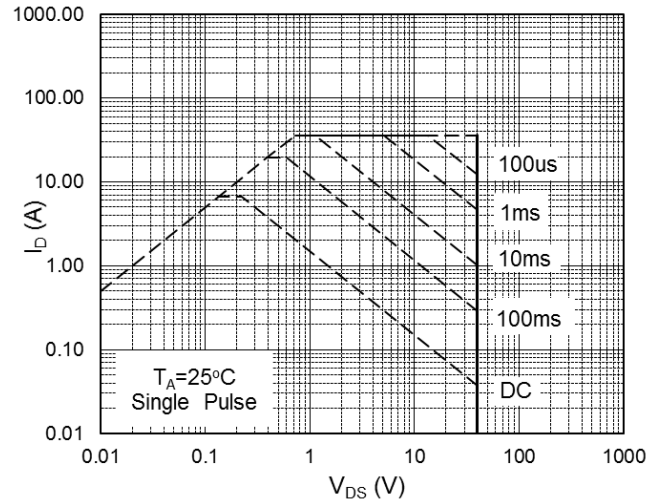


Fig.8 Safe Operating Area

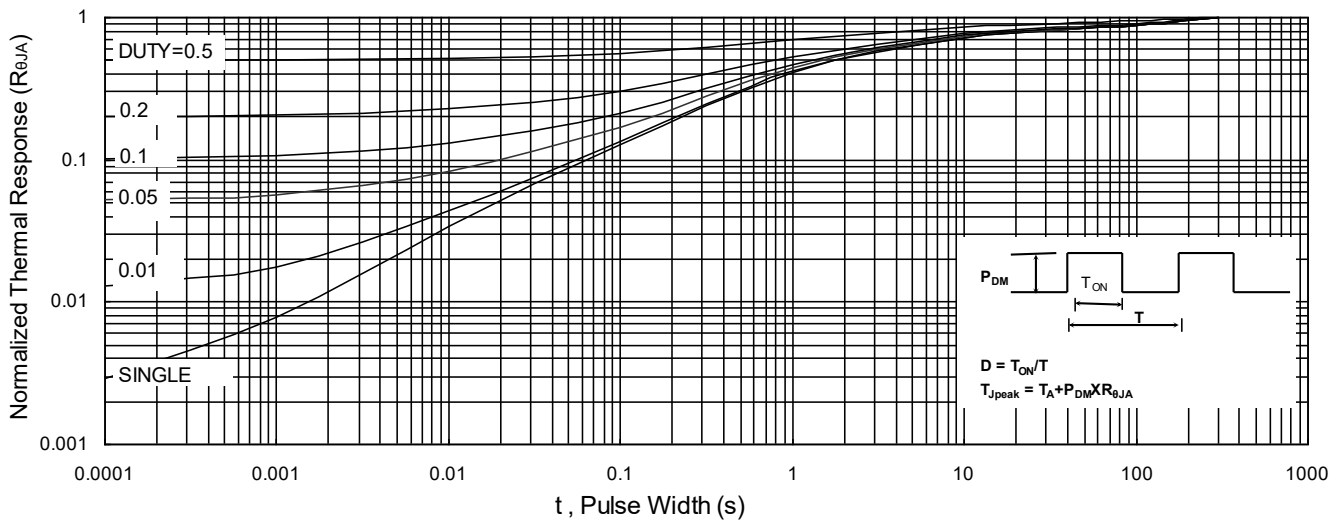


Fig.9 Normalized Maximum Transient Thermal Impedance

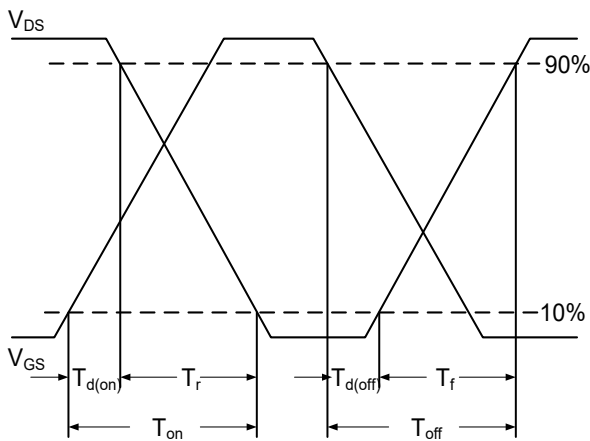


Fig.10 Switching Time Waveform

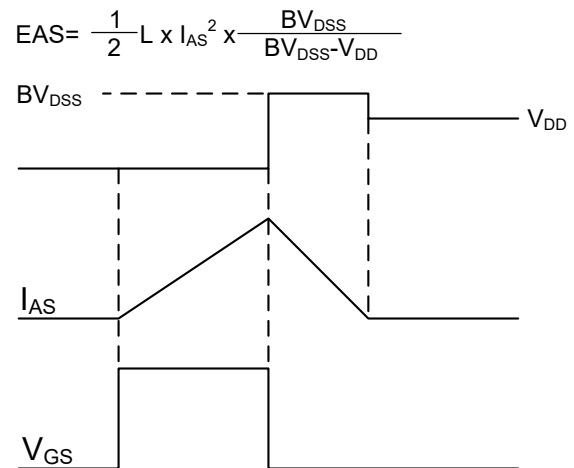
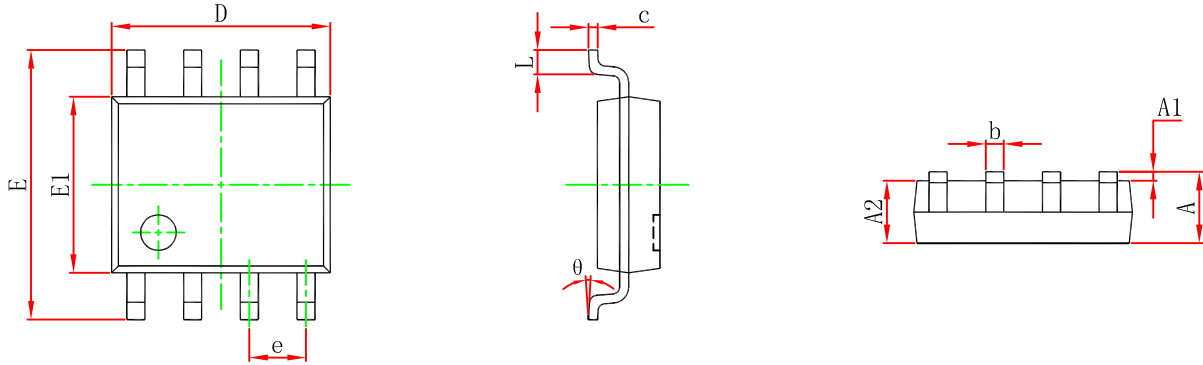


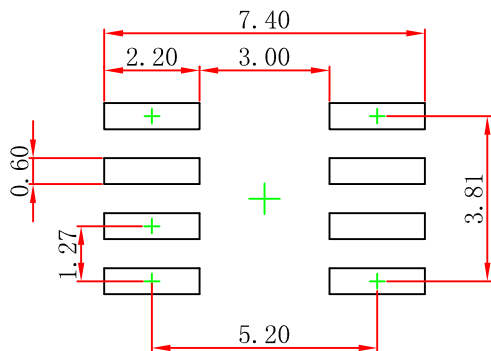
Fig.11 Unclamped Inductive Switching Waveform



SOP-8 Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.007 | 0.010 |
| D | 4.800 | 5.000 | 0.189 | 0.197 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| E | 5.800 | 6.200 | 0.228 | 0.244 |
| E1 | 3.800 | 4.000 | 0.150 | 0.157 |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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